Gordon Schmidt

List of Publications by Year
in descending order

32	272	933447 10	940533 16
papers	citations	h-index	g-index

32	32	32	417
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Optical Emission of Individual GaN Nanocolumns Analyzed with High Spatial Resolution. Nano Letters, 2015, 15, 5105-5109.	9.1	35
2	Nano-scale luminescence characterization of individual InGaN/GaN quantum wells stacked in a microcavity using scanning transmission electron microscope cathodoluminescence. Applied Physics Letters, 2014, 105, 032101.	3.3	30
3	Direct evidence of single quantum dot emission from GaN islands formed at threading dislocations using nanoscale cathodoluminescence: A source of single photons in the ultraviolet. Applied Physics Letters, 2015, 106, .	3.3	29
4	Growth of AlInN/GaN distributed Bragg reflectors with improved interface quality. Journal of Crystal Growth, 2015, 414, 105-109.	1.5	22
5	Direct imaging of Indium-rich triangular nanoprisms self-organized formed at the edges of InGaN/GaN core-shell nanorods. Scientific Reports, 2018, 8, 16026.	3.3	19
6	Growth and stacking fault reduction in semiâ€polar GaN films on planar Si(112) and Si(113). Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 507-510.	0.8	16
7	Compositionally graded InGaN layers grown on vicinal N-face GaN substrates by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2017, 465, 55-59.	1.5	16
8	Colorâ€Tunable 3D InGaN/GaN Multiâ€Quantumâ€Well Lightâ€Emittingâ€Diode Based on Microfacet Emission and Programmable Driving Power Supply. Advanced Optical Materials, 2021, 9, .	7.3	14
9	Growth of InGaN/GaN coreâ€“shell structures on selectively etched GaN rods by molecular beam epitaxy. Journal of Crystal Growth, 2014, 392, 5-10.	1.5	13
10	Metalorganic chemical vapor phase epitaxy of narrow-band distributed Bragg reflectors realized by GaN:Ge modulation doping. Journal of Crystal Growth, 2016, 440, 6-12.	1.5	11
11	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. Photonics Research, 2020, 8, 610.	7.0	8
12	Nanoscale cathodoluminescene imaging of IIIâ€nitrideâ€based LEDs with semipolar quantum wells in a scanning transmission electron microscope. Physica Status Solidi (B): Basic Research, 2016, 253, 112-117.	1.5	7
13	Ordered arrays of defect-free GaN nanocolumns with very narrow excitonic emission line width. Journal of Crystal Growth, 2019, 525, 125189.	1.5	7
14	Demonstration of lateral epitaxial growth of AlN on Si (1 1 1) at low temperatures by pulsed reactive sputter epitaxy. Journal of Crystal Growth, 2021, 571, 126250.	1.5	6
15	Embedded GaN nanostripes on câ€sapphire for DFB lasers with semipolar quantum wells. Physica Status Solidi (B): Basic Research, 2016, 253, 180-185.	1.5	5
16	Clustered quantum dots in single GaN islands formed at threading dislocations. Japanese Journal of Applied Physics, 2016, 55, 05FF04.	1.5	5
17	Advances in MBE Selective Area Growth of III-Nitride Nanostructures: From NanoLEDs to Pseudo Substrates. International Journal of High Speed Electronics and Systems, 2014, 23, 1450020.	0.7	4
18	Structural and optical nanoscale analysis of GaN coreâ€“shell microrod arrays fabricated by combined top-down and bottom-up process on Si(111). Japanese Journal of Applied Physics, 2016, 55, 05FF02.	1.5	4

#	Article	IF	Citations
19	Outstanding Reliability of Heavy-Ion-Irradiated AlInN/GaN on Silicon HFETs. IEEE Transactions on Nuclear Science, 2019, 66, 2417-2421.	2.0	4
20	Nanoscale Imaging of Structural and Optical Properties Using Helium Temperature Scanning Transmission Electron Microscopy Cathodoluminescence of Nitride Based Nanostructures. Microscopy and Microanalysis, 2016, 22, 600-601.	0.4	3
21	Cathodoluminescence nano-characterization of individual GaN/AlN quantum disks embedded in nanowires. Applied Physics Letters, 2020, 117, 133106.	3.3	3
22	Defect reduced selectively grown GaN pyramids as template for green InGaN quantum wells. Physica Status Solidi (B): Basic Research, 2016, 253, 67-72.	1.5	2
23	Nanoscale cathodoluminescence of stacking faults and partial dislocations in aâ€plane GaN. Physica Status Solidi (B): Basic Research, 2016, 253, 73-77.	1.5	2
24	Intensive luminescence from a thick, indium-rich In0.7Ga0.3N film. Japanese Journal of Applied Physics, 2019, 58, 065503.	1.5	2
25	Optical and Structural Properties of Nitride Based Nanostructures. Springer Series in Solid-state Sciences, 2020, , 135-201.	0.3	2
26	Direct nano-scale correlation of structural and optical properties of lattice matched AlInN/AlGaN DBRs using helium temperature scanning transmission electron microscopy cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1874-1875.	0.4	1
27	Direct imaging of GaN Pyramids covered by InGaN Single Quantum Well using nano-scale Scanning Transmission Electron Microscopy Cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1838-1839.	0.4	1
28	Cathodoluminescence directly performed in a transmission electron microscope: nanoscale correlation of structural and optical properties. Microscopy and Microanalysis, 2012, 18, 1834-1835.	0.4	1
29	Extended defects in GaN nanocolumns characterized by cathodoluminescence directly performed in a transmission electron microscope. Turkish Journal of Physics, 2014, 38, 323-327.	1.1	0
30	Nanoscale Cathodoluminescence of an InGaN Single Quantum Well Intersected by Individual Dislocations. Microscopy and Microanalysis, 2016, 22, 602-603.	0.4	0
31	Desorption induced formation of low-density GaN quantum dots: nanoscale correlation of structural and optical properties. Journal Physics D: Applied Physics, 2022, 55, 145102.	2.8	0
32	Direct Imaging of the Carrier Capture into Individual InP Quantum Dots of a Semiconductor Disk Laser Membrane. ACS Nano, 2022, 16, 4619-4628.	14.6	0